## EDC QuestionBank

- Q1. Explain Superconductivity and effect of magnetic field on it.
- **Q2.** Define relaxation time, collision time and mean free path. Derive mathematical relation between them.
- Q3. Classify the types of conducting materials. Also discuss their properties.
- **Q4.** Compare and explain electrical conductivity of metals, semiconductor and insulator on the basis of energy band diagram.
- **Q5.** Explain and compare diffusion and transition capacitance in diodes.
- **Q6.** Explain Zener Breakdown and Zener diode as voltage regulator.
- **Q7.** Derive and explain the continuity equation in semiconductor.
- **Q8.** Explain PN junction diode in biased and unbiased condition.
- **Q9.** Explain thermal conductivity and how it is related to Wiedmann-Franz law.
- **Q10.** Compare MOSFET, MISFET and MESFET.
- **Q11.** Compare and contrast between BJT & FET.
- Q12. Write short note on following:
  - i) TRIAC ii) DIAC iii) IGBT iv) PNPN diode
- Q13. Explain the negative resistance in diode & explain tunnel diode in detail.
- **Q14.** What do you mean by photoconductivity? Explain different types of photodiodes in detail.
- Q15. Explain construction, operation, characteristics and application of MOSFET (n & p channel).
- **Q16.** Compare CB, CC and CE configurations in deatil.
- Q17. Classify the types of conducting materials. Also discuss their properties.
- Q18. Explain construction, working and characteristics of solar cell.
- **O19.** Explain the various steps involved in planar technology for device fabrication.
- **Q20.** Explain construction, working and characteristics of TUNNEL diode.
- **Q21.** Explain n & p channel FET with the help of diagram. Also, discuss I/P & O/P characteristics.
- **Q22.** Explain breakdown mechanism and compare two types of breakdown in diodes.
- **Q23.** Discuss in detail w.r.t. their working & application on GUNN & IMPATT Diode.
- **Q24.** Compare D-MOSFET & E-MOSFET
- **Q25.** Explain working of BJT as an amplifier.
- **Q26.** Short answer questions:
  - *i.* Define drift velocity and drift current.
  - *ii.* Why FET is unipolar while BJT is bipolar device.
- *iii.* Explain the phenomenon of optical and electrical excitation in diode.
- iv. Explain the concept & significance of negative resistance in diode.
- v. Enlist the properties of photo-detectors.
- vi. Why common collector configuration knows as voltage buffer amplifier?
- *vii.* Why SCR is known as silicon controlled rectifier.
- viii. Explain and compare PIN and avalanche photodiode.
- *ix.* Why FET is known as Voltage controlled and BJT as current controlled device.
- x. Which type of semiconductor is used in manufacturing of LED and why?

- Why silicon is generally used in manufacturing diodes? Compare LED & LASER. xi.
- xii.